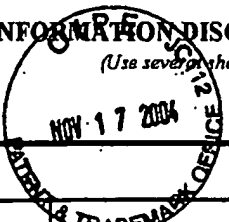


# INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)



Docket Number (Optional)

FIS920030078US2 (16422A)

Application Number

Unassigned

Applicant(s)

Sadanand V. Deshpande, et al.

10/75/831

Filing Date

Herewith

Group Art Unit

Unassigned

## U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ES		3,602,841	08/31/71	McGroddy			
		4,655,415	05/12/87	Esaki, et al.			
		4,853,076	08/01/89	Tsaur, et al.			
		4,855,245	08/08/89	Neppl, et al.			
		4,952,524	08/28/90	Lee, et al.			

## U.S. PATENT APPLICATION PUBLICATIONS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		2001/0009784 A1	07/26/01	Ma, et al			
		2002/0074598 A1	06/20/02	Doyle, et al.			
		2002/0086472 A1	07/04/02	Roberds, et al.			
		2002/0086497 A1	07/04/02	Kwok			

## FOREIGN PATENT DOCUMENTS

REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
	EPO 01/62362	26/06/89	Hasegawa, Michihiko				
	EP 1 174 928 A1	01/23/02	Hitachi Ltd.				
	EP 0 967 636 A2	12/29/1999	Rengarajan, et al.				
	WO 02/454156 A2	06/06/2002	Armstrong et al.				
	WO 94/27317	05/06/1993	Winnerl, et al.				

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	Rim, et al., "Transconductance Enhancement in Deep Submicron Strained-Si n-MOSFETs", International Electron Devices Meeting, 26, 8, 1, IEEE, September 1998;
ES	Rim, et al. "Characteristics and Device Design of Sub-100 nm Strained Si N- and PMOSFETs", 2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99;

EXAMINER

ES

DATE CONSIDERED

3-5-05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>FIS920030078US2 (16422A)</b>		Application Number <b>10/257,831</b> <b>Unassigned</b>			
				Applicant(s) <b>Sadanand V. Deshpande, et al.</b>					
				Filing Date <b>Herewith</b>		Group Art Unit <b>Unassigned 2815</b>			

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EH		4,958,213	09/18/90	Eklund, et al			
		5,006,913	04/09/91	Sugahara, et al			
		5,060,030	10/22/91	Hoke			
		5,081,513	01/14/92	Jackson, et al			
		5,108,843	04/28/92	Ohtaka, et al			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EH		2002/0090791 A1	07/11/02	Doyle, et al			
		2003/0032261 A1	02/13/03	Yeh, et al			
		2003/0040158 A1	02/27/03	Saitoh			
		2003/0057184 A1	03/27/03	Yu, et al			

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS		(Including Author, Title, Date, Pertinent Pages, Etc.)
EH		Scott, et al. "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999;
EH		Ootsuka, et al. "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Device Meeting, 23.5.1, IEEE, April 2000;

EXAMINER <div style="text-align: center; font-size: 1.5em;">EH</div>	DATE CONSIDERED <div style="text-align: center; font-size: 1.5em;">3-5-05</div>
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**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

Docket Number (Optional)

FIS920030078US2 (16422A)

Application Number 10/751831  
Unassigned

Applicant(s)

Sadanand V. Deshpande, et al.

Filing Date

Herewith

Group Art Unit

Unassigned 2815

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>EP</u>		5,134,085	07/28/02	Gilgen, et al			
		5,310,446	05/10/94	Konishi, et al			
		5,354,695	10/11/94	Leedy			
		5,371,399	12/06/94	Burroughes, et al			
<u>EP</u>		5,391,510	02/21/95	Hsu, et al			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>EP</u>		2003/0067035 A1	04/10/03	Tews, et al			

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>EP</u>		Ito, et al. "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000;
<u>EP</u>		Shimizu, et al. "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001;

EXAMINER

EP

DATE CONSIDERED

3-5-05

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**INFORMATION DISCLOSURE CITATION**  
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Docket Number (Optional)

FIS920030078US2 (16422A)

Application Number

10/25/83/  
Unassigned

Applicant(s)

Sadanand V. Deshpande, et al.

Filing Date

Herewith

Group Art Unit

2815  
Unassigned

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EH		5,459,346	10/17/95	Asakawa, et al			
		5,471,948	12/05/95	Burroughes, et al.			
		5,557,122	09/17/96	Shrivastava, et al.			
		5,561,302	10/01/96	Candelaria			
EH		5,565,697	10/15/96	Asakawa, et al			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)

EH		Ota, et al. "Novel Locally Strained Channel Technique for high Performance 55nm CMOS", International Electron Devices Meeting, 2.2.1, IEEE, February 2002.
EH		Ouyang, et al. "Two-Dimensional Bandgap Engineering in a Novel Si/SiGe pMOSFETS With Enhanced Device Performance and Scalability", Microelectronics Research Center, pp 151-154, 2000 IEEE.

EXAMINER

E.O.

DATE CONSIDERED

3-5-05

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**INFORMATION DISCLOSURE CITATION**  
(Use several sheets if necessary)

Docket Number (Optional)

FIS920030078US2 (16422A)

Application Number 0/751831  
Unassigned

Applicant(s)

Sadanand V. Deshpande, et al.

Filing Date

Herewith

Group Art Unit

Unassigned 2815

**U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<u>EH</u>		5,571,741	11/05/96	Leedy, et al			
		5,592,007	01/07/97	Leedy			
		5,592,018	01/07/97	Leedy			
		5,670,798	09/23/97	Schetzina			
<u>EH</u>		5,679,965	10/21/97	Schetzina			

**U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

**FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

<u>EH</u>		Sayama et al., "Effect of <Channel Direction for High Performance SCE Immune pMOSFET with Less Than 0.15um Gate Length" ULSI Development Center, pp27.5.1-27.5.4, 1999 IEEE.

EXAMINER

EH

DATE CONSIDERED

3-5-05

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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>FIS920030078US2 (16422A)</b>		Application Number <b>10/751831</b> <b>Unassigned</b>		
				Applicant(s) <b>Sadanand V. Deshpande, et al.</b>				
				Filing Date <b>Herewith</b>		Group Art Unit <b>Unassigned 2815</b>		
<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
EH		5,960,297	09/28/99	Saki				
		5,989,978	11/23/99	Peidous				
		6,008,126	12/28/99	Leedy				
		6,025,280	02/15/00	Brady, et al				
EH		6,046,464	04/04/00	Schetzina				
<b>U.S. PATENT APPLICATION PUBLICATIONS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
<b>FOREIGN PATENT DOCUMENTS</b>								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
EXAMINER <span style="float: right;">EH</span>				DATE CONSIDERED <span style="float: right;">3-5-05</span>				
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# **INFORMATION DISCLOSURE CITATION**

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Docket Number (Optional)

FIS920030078US2 (16422A)

Application Number

Unassigned

10/75/831

Applicant(s)

Sadanand V. Deshpande, et al.

Filing Date

Herewith

Group Art Unit

Unassigned

28/5

## **U.S. PATENT DOCUMENTS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
EO		6,221,735	04/24/01	Manley, et al			
		6,228,694	05/08/01	Doyle, et al			
		6,246,095	06/12/01	Brady, et al			
		6,255,169	07/03/01	Li, et al			
EO		6,261,964	07/17/01	Wu, et al			

## **U.S. PATENT APPLICATION PUBLICATIONS**

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## **FOREIGN PATENT DOCUMENTS**

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

## **OTHER DOCUMENTS**

(Including Author, Title, Date, Pertinent Pages, Etc.)


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E. D.

DATE CONSIDERED

3-5-05

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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. FIS920030078US2 (16422A)		SERIAL NO. Unassigned <b>10/151831</b>	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (Use several sheets if necessary)				APPLICANTS Sadanand V. Deshpande, et al.			
				FILING DATE Herewith		GROUP ART UNIT Unassigned <b>2815</b>	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<b>E81</b>		6,265,317	07/24/01	Chiu et al.			
		6,274,444	08/14/01	Wang			
		6,281,532 B1	08/28/01	Doyle et al.			
		6,284,623	09/04/01	Zhang et al.			
		6,284,626	09/04/01	Kim			
<b>E81</b>		6,319,794	11/20/01	Akatsu, et al.			
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
							YES      NO
OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER <b>E81</b>				DATE CONSIDERED <b>3-5-05</b>			
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>FIS920030078US2 (16422A)</b>		Application Number <b>10/751831</b> <del>Unassigned</del>	
				Applicant(s) <b>Sadanand V. Deshpande, et al.</b>			
				Filing Date <b>Herewith</b>		Group Art Unit <b>Unassigned 2815</b>	

U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ED		6,361,885	03/26/02	Chou			
		6,362,082	03/26/02	Doyle, et al			
		6,368,931	04/09/02	Kuhn, et al			
		6,403,486	06/11/02	Lou			
ED		6,403,975	06/11/02	Brunner, et al			

U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO

OTHER DOCUMENTS			(Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER <span style="float: right; font-size: 1.5em;">ED</span>	DATE CONSIDERED <span style="float: right; font-size: 1.5em;">3-5-05</span>
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Sheet of

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Form PTO-1449

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.  
FIS92003007BUS2 (16422A)SERIAL NO.  
Unassigned 10/75/831INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT

(Use several sheets if necessary)

APPLICANTS  
Sadanand V. Deshpande, et al.FILING DATE  
HerewithGROUP ART UNIT  
Unassigned 2815

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
ESJ	6,406,973 B1	06/18/02	Lee			
	6,461,936	10/18/02	Von Ehrenwall			
	6,476,462 B1	11/05/02	Shimizu et al.			
	6,493,497	12/10/02	Ramdani, et al.			
	6,498,358	12/24/02	Lach, et al			
	6,501,121	12/31/02	Yu, et al.			
ESJ	6,506,652	01/14/03	Jan, et al			

## FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

## OTHER PRIOR ART (Including Author, Title, Date, Pertinent Pages, Etc.)


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ESJ

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3-5-05

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<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>FIS920030078US2 (16422A)</b>		Application Number <b>10/751,831</b> <del>Unassigned</del>		
				Applicant(s) <b>Sadanand V. Deshpande, et al.</b>				
				Filing Date <b>Herewith</b>		Group Art Unit <b>Unassigned 2815</b>		
U.S. PATENT DOCUMENTS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
		6,509,618	01/21/03	Jan, et al				
		6,521,964	02/18/03	Jan, et al				
		6,531,369	03/11/03	Ozkan, et al				
		6,531,740	03/11/03	Bosco, et al				
U.S. PATENT APPLICATION PUBLICATIONS								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
FOREIGN PATENT DOCUMENTS								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
EXAMINER				DATE CONSIDERED <b>3-5-05</b>				
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